

4V Drive Pch MOSFET

RT1E040RP

Structure

Silicon P-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) High power package.
- 3) 4V drive.

Application

Switching

Packaging specifications

| | • . | | |
|----------|------------------------------|--------|--|
| Type | Package | Taping | |
| | Code | TR | |
| | Basic ordering unit (pieces) | 3000 | |
| RT1E040R | 0 | | |

● Absolute maximum ratings (Ta = 25°C)

| Parameter | | Symbol | Limits | Unit |
|--------------------------------|------------|--------------------|-------------|------|
| Drain-source voltage | | V_{DSS} | - 30 | V |
| Gate-source voltage | | V_{GSS} | ±20 | V |
| Drain current | Continuous | I _D | ±4 | Α |
| | Pulsed | I _{DP} *1 | ± 16 | Α |
| Source current (Body Diode) | Continuous | I _S | -1 | Α |
| | Pulsed | I _{SP} *1 | -16 | Α |
| Power dissipation | | P _D *2 | 1.25 | W |
| Channel temperature | | Tch | Tch 150 | |
| Range of storage temperature | | Tstg | -55 to +150 | °C |

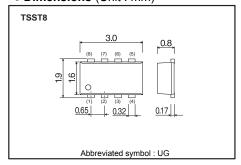
^{*1} Pw≤10µs, Duty cycle≤1%

• Thermal resistance

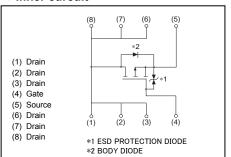
| Parameter | Symbol | Limits | Unit |
|--------------------|-------------|--------|------|
| Channel to Ambient | Rth (ch-a)* | 100 | °C/W |

^{*}Mounted on a ceramic board.

● Dimensions (Unit : mm)



• Inner curcuit



^{*2} Mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|-----------------------|------|------|------|----------|---|
| Gate-source leakage | I_{GSS} | 1 | - | ±10 | μA | V_{GS} =±20V, V_{DS} =0V |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | -30 | - | - | ٧ | I _D =-1mA, V _{GS} =0V |
| Zero gate voltage drain current | I _{DSS} | 1 | - | -1 | μA | V_{DS} =-30V, V_{GS} =0V |
| Gate threshold voltage | V _{GS (th)} | -1.0 | 1 | -2.5 | V | V_{DS} =-10V, I_{D} =-1mA |
| Static ducin accuracy an atata | * | ı | 32 | 45 | | I _D =-4A, V _{GS} =-10V |
| Static drain-source on-state resistance | R _{DS (on)} | ı | 45 | 63 | mΩ | $I_D = -2A$, $V_{GS} = -4.5V$ |
| | | 1 | 52 | 72 | | I _D =-2A, V _{GS} =-4.0V |
| Forward transfer admittance | IY _{fs} I* | 2.7 | - | - | S | I _D =-4A, V _{DS} =-10V |
| Input capacitance | C _{iss} | 1 | 1000 | - | pF | V _{DS} =-10V |
| Output capacitance | C _{oss} | 1 | 150 | ı | pF | V _{GS} =0V |
| Reverse transfer capacitance | C _{rss} | 1 | 130 | - | pF | f=1MHz |
| Turn-on delay time | t _{d(on)} * | 1 | 15 | ı | ns | I _D =-2A, V _D ; -15V |
| Rise time | t _r * | 1 | 30 | - | ns | V _{GS} =-10V |
| Turn-off delay time | t _{d(off)} * | 1 | 85 | - | ns | R_L =7.5 Ω |
| Fall time | t _f * | 1 | 45 | ı | ns | R_G =10 Ω |
| Total gate charge | Q _g * | - | 10.5 | - | nC | I _D =-4A, V _{DD} ≒-15V |
| Gate-source charge | Q _{gs} * | - | 3.0 | - | nC | V_{GS} =-5V R_L =3.8 Ω |
| Gate-drain charge | Q _{gd} * | - | 3.3 | - | nC | R_G =10 Ω |

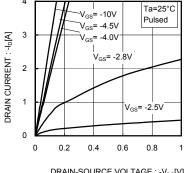
^{*}Pulsed

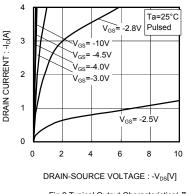
●Body diode characteristics (Source-Drain) (Ta = 25°C)

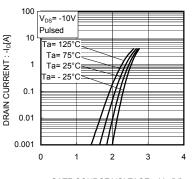
| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|--|
| Forward Voltage | V _{SD} * | - | - | -1.2 | V | I _s =-4A, V _{GS} =0V |

^{*}Pulsed

Electrical characteristics curves



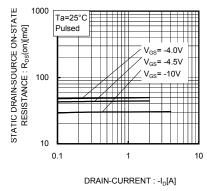


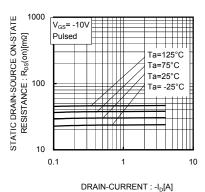


DRAIN-SOURCE VOLTAGE: -VDS[V] Fig.1 Typical Output Characteristics(I)

Fig.2 Typical Output Characteristics(II)

GATE-SOURCE VOLTAGE : $-V_{GS}[V]$ Fig.3 Typical Transfer Characteristics





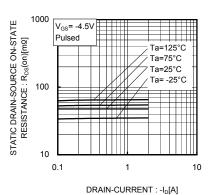
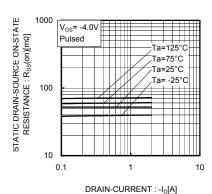


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)



FORWARD TRANSFER ADMITTANCE: |Yfs| [S] V_{DS}= -10V Pulsed -25°C Ta=25°C Ta=75°C Ta=125°C 0.1 0.01 0.1 10

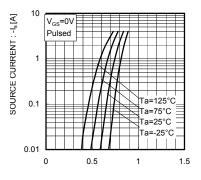
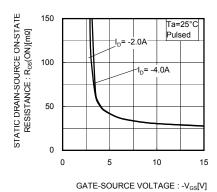


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

DRAIN-CURRENT : -I_D[A] Fig.8 Forward Transfer Admittance vs. Drain Current

SOURCE-DRAIN VOLTAGE : $-V_{SD}[V]$ Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

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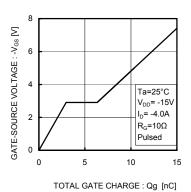
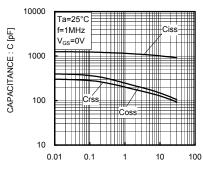


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

Fig.11 Switching Characteristics

Fig.12 Dynamic Input Characteristics



DRAIN-SOURCE VOLTAGE : -V_{DS}[V]
Fig.13 Typical Capacitance
vs. Drain-Source Voltage

Measurement circuits

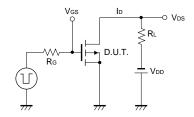


Fig.1-1 Switching Time Measurement Circuit

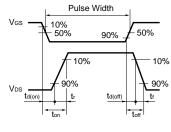


Fig.1-2 Switching Waveforms

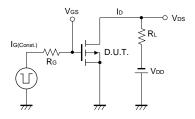


Fig.2-1 Gate Charge Measurement Circuit

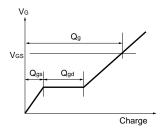


Fig.2-2 Gate Charge Waveform

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